

## Schottky Power Diode, 40A

**Features**

- Fast Switching
- Low forward voltage drop
- High surge capability
- High efficiency, low power loss
- Normal and Reverse polarity



DO-203AB (DO-5)

Maximum Ratings ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)						
Parameter	Test Conditions	Symbol	1N5832(R)	1N5833(R)	1N5834(R)	Units
Repetitive peak reverse voltage		$V_{RRM}$	20	30	40	V
RMS reverse voltage		$V_{RMS}$	14	21	28	V
DC blocking voltage		$V_{DC}$	20	30	40	V
Continuous forward current	$T_C \leq 100^\circ\text{C}$	$I_F$	40	40	40	A
Surge non-repetitive forward current, half-sine wave	$T_C = 25^\circ\text{C}$	$I_{FSM}$	800	800	800	A
Forward voltage	$I_F = 40\text{ A}$ $T_J = 25^\circ\text{C}$	$V_F$	0.52	0.55	0.58	V
Reverse current	$V_R = 10\text{V}, T_J = 25^\circ\text{C}$	$I_R$	20	20	20	mA
	$V_R = 10\text{V}, T_J = 125^\circ\text{C}$		250	250	250	

Thermal & Mechanical Specifications ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)					
Parameters	Symbol	1N5832(R)	1N5833(R)	1N5834(R)	Units
Maximum thermal resistance, junction to case	$R_{th(jc)}$	1.5			$^\circ\text{C/W}$
Operating junction temperature range	$T_J$	-65 to 150			$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 to 175			$^\circ\text{C}$
Mounting torque (non-lubricated threads)	F	4.0			Nm
Approximate allowable weight	W	17.0			g

